

20V P-Channel Enhancement Mode Power MOSFET

Description

The S20P110K uses advanced Trench technology and designs to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.

Features

- High density cell design for Low $R_{DS(on)}$
- Voltage controlled small signal switch
- Rugged and reliable
- High saturation current capability
- ESD protected Gate HBM 1KV

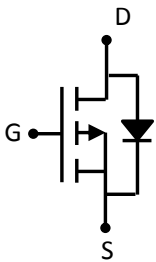
Applications

- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch

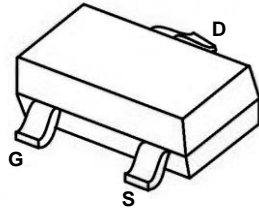
MOSFET Product Summary

V_{DSS}	$R_{DS(ON)}$ @ $V_{GS} = -4.5V$	$R_{DS(ON)}$ @ $V_{GS} = -2.5V$	I_D
-20V	110m Ω	140m Ω	-2.3A

Dimensions and Pin Configuration



Circuit diagram



SOT-23

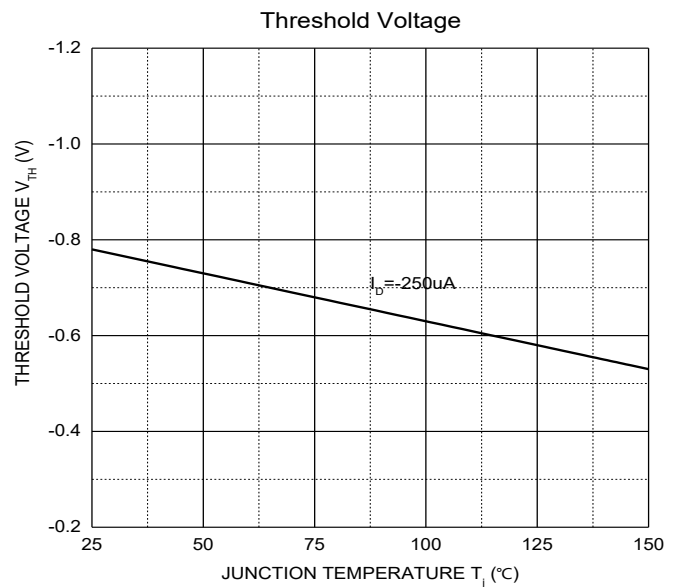
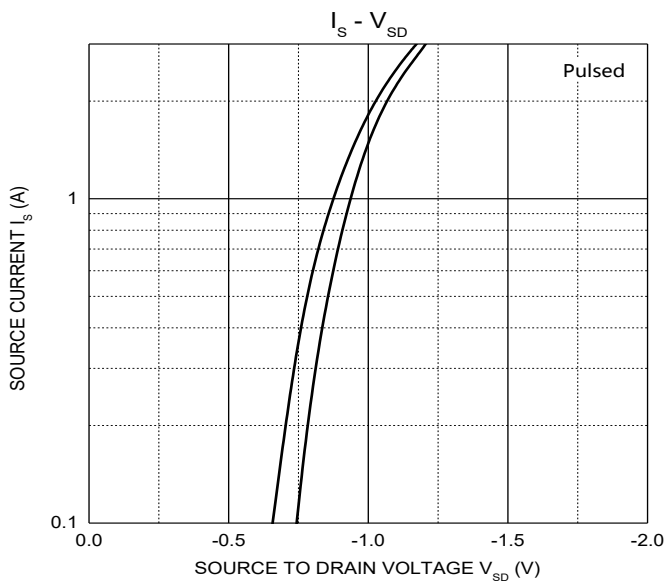
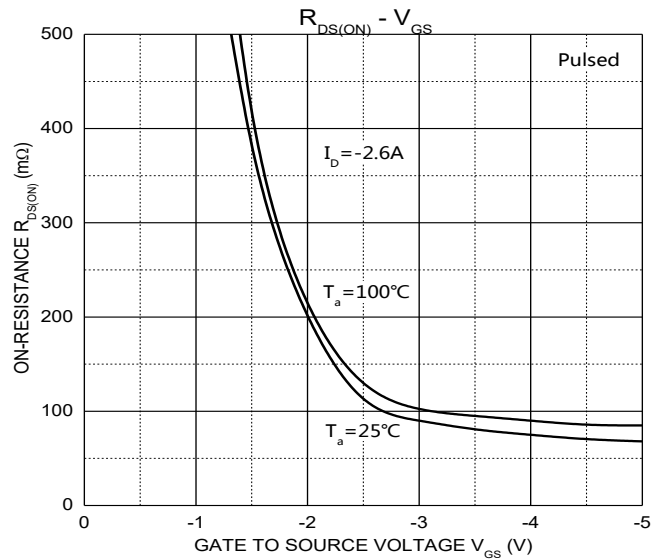
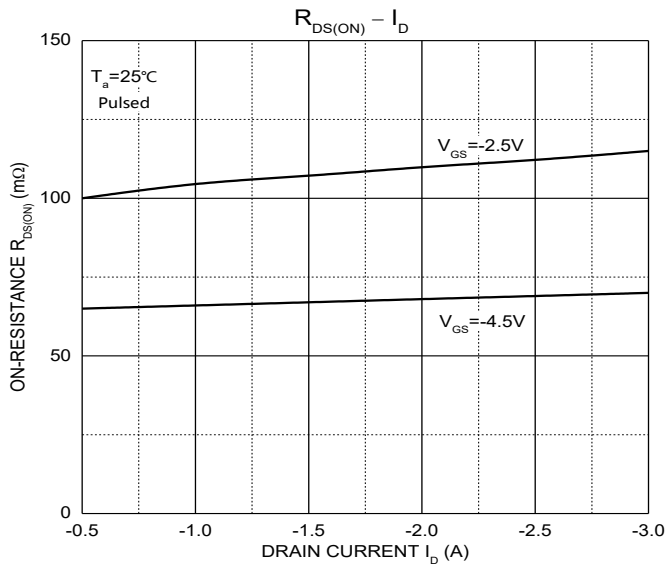
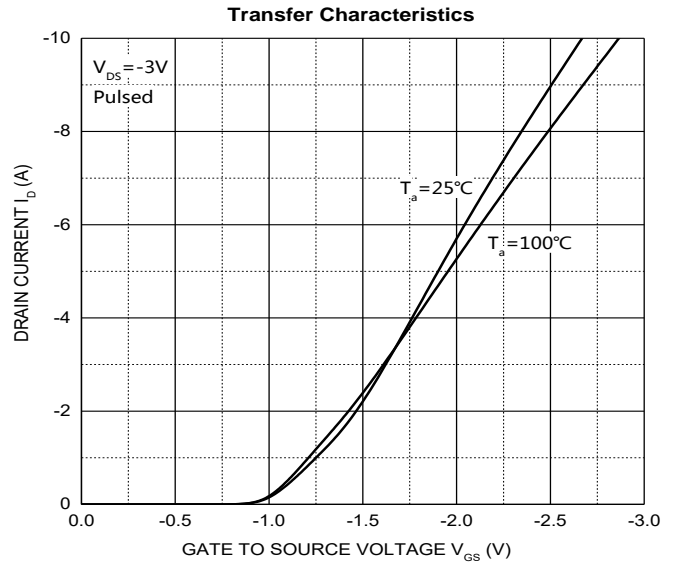
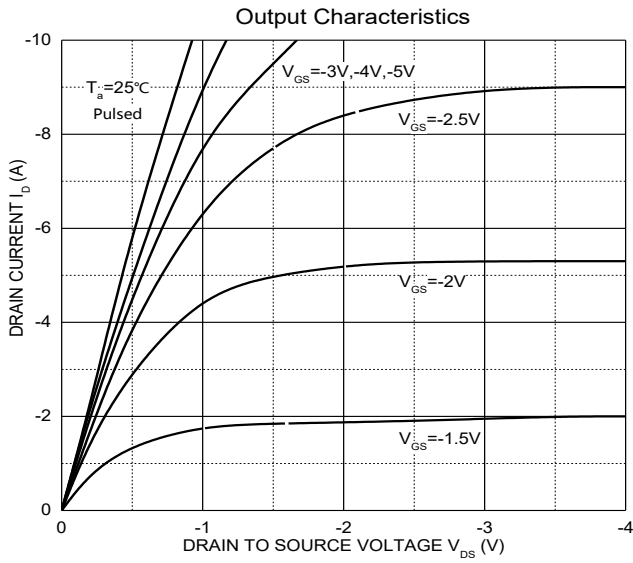
Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

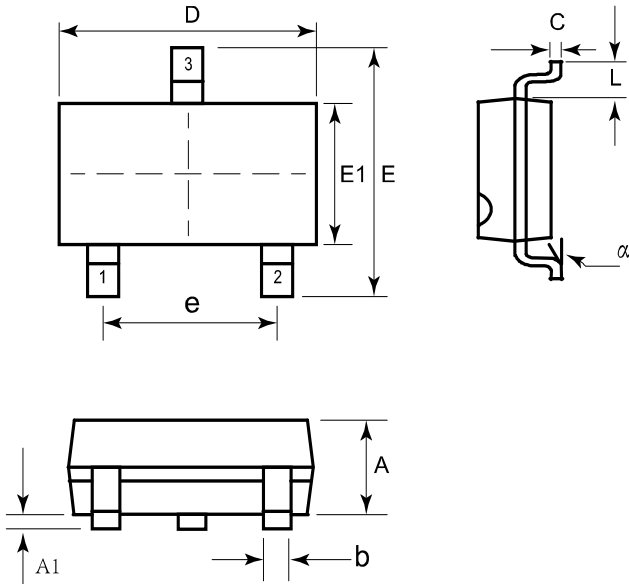
Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 8	V
Continuous Drain Current	I_D	-2.3	A
Pulsed Drain Current ($t=300\mu\text{s}$)	I_{DM}	-10	A
Power Dissipation	P_D	0.35	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

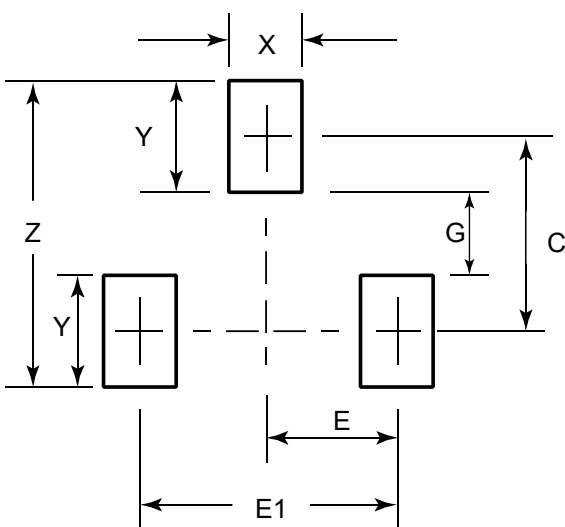
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-20			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -20V, V_{GS} = 0V$			-1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 8V, V_{DS} = 0V$			± 100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.4	-0.7	-1	V
Drain-source on-resistance	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -3A$		83	110	m Ω
		$V_{GS} = -2.5V, I_D = -2A$		110	140	
Forward transconductance	g_{FS}	$V_{DS} = -5V, I_D = -2A$	5			S
Dynamic characteristics						
Input Capacitance	C_{iss}	$V_{DS} = -10V, V_{GS} = 0V, f = 1MHz$		405		pF
Output Capacitance	C_{oss}			75		
Reverse Transfer Capacitance	C_{rss}			55		
Gate resistance	R_g	$f = 1MHz$		6		Ω
Total Gate Charge	Q_g	$V_{DS} = -10V, V_{GS} = -2.5V, I_D = -3A$		3.3	12	nC
Gate-Source Charge	Q_{gs}			0.7		
Gate-Drain Charge	Q_{gd}			1.3		
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -10V, V_{GEN} = -4.5V, I_D = -1A$ $R_L = 10\Omega, R_{GEN} = 1\Omega$		11		ns
Turn-on rise time	t_r			35		
Turn-off delay time	$t_{d(off)}$			30		
Turn-off fall time	t_f			10		
Source-Drain Diode characteristics						
Diode forward current	I_S	$T_C = 25^\circ\text{C}$			-2.3	A
Diode pulsed forward current ¹⁾	I_{SM}				-10	A
Diode Forward voltage	V_{DS}	$V_{GS} = 0V, I_S = -1.3A$			-1.2	V

Typical Characteristics



SOT-23 Package Outline Drawing


SYM	DIMENSIONS					
	INCHES			MILLIMETERS		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.035	0.037	0.040	0.88	0.95	1.02
A1	0.000	-	0.004	0.01	-	0.10
b	0.012	-	0.020	0.30	-	0.51
C	0.003	-	0.007	0.08	-	0.18
D	0.110	0.114	0.120	2.80	2.90	3.04
E	0.082	0.093	0.104	2.10	2.37	2.64
E1	0.047	0.051	0.055	1.20	1.30	1.40
e	0.075 BSC			1.90 BSC		
L	0.022 BSC			0.55 BSC		
alpha	0°		8°	0°		8°

Suggested Land Pattern


SYM	DIMENSIONS	
	MILLIMETERS	INCHES
C	2.20	0.087
E	0.95	0.037
E1	1.90	0.075
G	0.80	0.031
X	1.00	0.039
Y	1.40	0.055
Z	3.60	0.141